

### FEATURES

- Very low offset voltage**  
125  $\mu$ V maximum
- Supply current:** 215  $\mu$ A/amp typical
- Input bias current:** 200 pA maximum
- Low input offset voltage drift:** 1.2  $\mu$ V/ $^{\circ}$ C maximum
- Very low voltage noise:** 11 nV/ $\sqrt$ Hz
- Operating temperature:**  $-40^{\circ}$ C to  $+125^{\circ}$ C
- Rail-to-rail output swing**
- Unity gain stable**
- $\pm 2.5$  V to  $\pm 15$  V operation**

### APPLICATIONS

- Portable precision instrumentation**
- Laser diode control loops**
- Strain gage amplifiers**
- Medical instrumentation**
- Thermocouple amplifiers**

### GENERAL DESCRIPTION

The AD8622 is a dual, precision rail-to-rail output operational amplifier with a low supply current of only 350  $\mu$ A maximum over temperature and supply voltages. It also offers ultralow offset, drift, and voltage noise combined with very low input bias current over the full operating temperature range.

With typical offset voltage of only 10  $\mu$ V, offset drift of 0.5  $\mu$ V/ $^{\circ}$ C, and noise of only 0.2  $\mu$ V p-p (0.1 Hz to 10 Hz), it is perfectly suited for applications where large error sources cannot be tolerated. Many systems can take advantage of the low noise, dc precision, and rail-to-rail output swing provided by the AD8622 to maximize the signal-to-noise ratio and dynamic range for low power operation. The AD8622 is specified for the extended industrial temperature range of  $-40^{\circ}$ C to  $+125^{\circ}$ C and is available in lead-free SOIC and MSOP packages.

### PIN CONFIGURATIONS

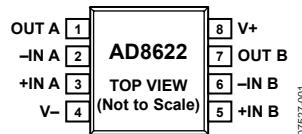


Figure 1. 8-Lead Narrow-Body SOIC



Figure 2. 8-Lead MSOP

Rev. 0

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Table 1. Low Power Op Amps

Supply	40 V	36 V	12 V to 16 V	5 V
Single	<a href="#">OP97</a>	<a href="#">OP777</a> <a href="#">OP1177</a>	<a href="#">OP196</a> <a href="#">AD8663</a>	<a href="#">AD8603</a>
Dual	<a href="#">OP297</a>	<a href="#">OP727</a> <a href="#">OP2177</a> <a href="#">AD706</a>	<a href="#">OP296</a> <a href="#">AD8667</a>	<a href="#">AD8607</a>
Quad	<a href="#">OP497</a>	<a href="#">OP747</a> <a href="#">OP4177</a> <a href="#">AD704</a>	<a href="#">OP496</a> <a href="#">AD8669</a>	<a href="#">AD8609</a>

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## REVISION HISTORY

7/09—Revision 0: Initial Version

## SPECIFICATIONS

### ELECTRICAL CHARACTERISTICS— $\pm 15$ V OPERATION

$V_S = \pm 15$  V,  $V_{CM} = 0$  V,  $T_A = +25^\circ\text{C}$ , unless otherwise specified.

Table 2.

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
INPUT CHARACTERISTICS						
Offset Voltage	$V_{OS}$	$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	10	125	230	$\mu\text{V}$
Offset Voltage Drift	$\Delta V_{OS}/\Delta T$	$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	0.5	1.2	1.8	$\mu\text{V}/^\circ\text{C}$
Input Bias Current	$I_B$	$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	45	200	500	$\text{pA}$
Input Offset Current	$I_{OS}$	$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	35	200	500	$\text{pA}$
Input Voltage Range						V
Common-Mode Rejection Ratio	CMRR	$V_{CM} = -13.8$ V to $+13.8$ V $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	125	135	140	dB
Open-Loop Gain	$A_{VO}$	$R_L = 10 \text{ k}\Omega$ , $V_O = -13.5$ V to $+13.5$ V $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	125	137	140	dB
Input Resistance, Differential Mode	$R_{INDM}$		1			$\text{G}\Omega$
Input Resistance, Common Mode	$R_{INCM}$		1			$\text{T}\Omega$
Input Capacitance, Differential Mode	$C_{INDM}$		5.5			$\text{pF}$
Input Capacitance, Common Mode	$C_{INCM}$		3			$\text{pF}$
OUTPUT CHARACTERISTICS						
Output Voltage High	$V_{OH}$	$R_L = 100 \text{ k}\Omega$ to ground $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	14.94	14.97	15.0	V
		$R_L = 10 \text{ k}\Omega$ to ground $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	14.84			V
		$R_L = 100 \text{ k}\Omega$ to ground $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	14.86	14.89	14.92	V
		$R_L = 10 \text{ k}\Omega$ to ground $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	14.75			V
Output Voltage Low	$V_{OL}$	$R_L = 100 \text{ k}\Omega$ to ground $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		-14.97	-14.94	V
		$R_L = 100 \text{ k}\Omega$ to ground $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			-14.92	V
		$R_L = 10 \text{ k}\Omega$ to ground $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		-14.89	-14.90	V
		$R_L = 10 \text{ k}\Omega$ to ground $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			-14.80	V
Short-Circuit Current	$I_{SC}$			$\pm 40$		$\text{mA}$
Closed-Loop Output Impedance	$Z_{OUT}$	$f = 1 \text{ kHz}$ , $A_V = 1$		1.5		$\Omega$
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	$V_S = \pm 2.0$ V to $\pm 18.0$ V $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	125	145	160	dB
Supply Current/Amplifier	$I_{SY}$	$I_O = 0 \text{ mA}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		215	250	$\mu\text{A}$
					350	$\mu\text{A}$
DYNAMIC PERFORMANCE						
Slew Rate	SR	$R_L = 10 \text{ k}\Omega$ , $A_V = 1$		0.48		$\text{V}/\mu\text{s}$
Gain Bandwidth Product	GBP	$C_L = 35 \text{ pF}$ , $A_V = 1$		600		kHz
Phase Margin	$\Phi_M$	$C_L = 35 \text{ pF}$ , $A_V = 1$		72		Degrees
NOISE PERFORMANCE						
Voltage Noise	$e_n \text{ p-p}$	$f = 0.1 \text{ Hz}$ to $10 \text{ Hz}$		0.2		$\mu\text{V p-p}$
Voltage Noise Density	$e_n$	$f = 1 \text{ kHz}$		11		$\text{nV}/\sqrt{\text{Hz}}$
Uncorrelated Current Noise Density	$i_n$	$f = 1 \text{ kHz}$		0.15		$\text{pA}/\sqrt{\text{Hz}}$
Correlated Current Noise Density	$i_n$	$f = 1 \text{ kHz}$		0.06		$\text{pA}/\sqrt{\text{Hz}}$

**ELECTRICAL CHARACTERISTICS— $\pm 2.5$  V OPERATION** $V_S = \pm 2.5$  V,  $V_{CM} = 0$  V,  $T_A = +25^\circ\text{C}$ , unless otherwise specified.**Table 3.**

<b>Parameter</b>	<b>Symbol</b>	<b>Conditions</b>	<b>Min</b>	<b>Typ</b>	<b>Max</b>	<b>Unit</b>
INPUT CHARACTERISTICS						
Offset Voltage	$V_{OS}$	$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	10	125	230	$\mu\text{V}$
Offset Voltage Drift	$\Delta V_{OS}/\Delta T$	$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	0.5	1.2	1.2	$\mu\text{V}/^\circ\text{C}$
Input Bias Current	$I_B$	$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	30	200	400	pA
Input Offset Current	$I_{OS}$	$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	25	200	300	pA
Input Voltage Range		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	-1.3	+1.3	+1.3	V
Common-Mode Rejection Ratio	CMRR	$V_{CM} = -1.3$ V to $+1.3$ V $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	110	120	107	dB
Open-Loop Gain	$A_{VO}$	$R_L = 10 \text{ k}\Omega$ , $V_O = -2.0$ V to $+2.0$ V $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	118	135	109	dB
Input Resistance, Differential Mode	$R_{INDM}$		1			$\text{G}\Omega$
Input Resistance, Common Mode	$R_{INCM}$		1			$\text{T}\Omega$
Input Capacitance, Differential Mode	$C_{INDM}$		5.5			pF
Input Capacitance, Common Mode	$C_{INCM}$		3			pF
OUTPUT CHARACTERISTICS						
Output Voltage High	$V_{OH}$	$R_L = 100 \text{ k}\Omega$ to ground $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	2.45	2.49	2.41	V
		$R_L = 10 \text{ k}\Omega$ to ground $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	2.40	2.45	2.36	V
Output Voltage Low	$V_{OL}$	$R_L = 100 \text{ k}\Omega$ to ground $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	-2.49	-2.45	-2.41	V
		$R_L = 10 \text{ k}\Omega$ to ground $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	-2.45	-2.40	-2.36	V
Short-Circuit Current	$I_{SC}$		$\pm 30$			mA
Closed-Loop Output Impedance	$Z_{OUT}$	$f = 1 \text{ kHz}$ , $A_V = 1$	2			$\Omega$
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	$V_S = \pm 2.0$ V to $\pm 18.0$ V $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	125	145	120	dB
Supply Current/Amplifier	$I_{SY}$	$I_O = 0 \text{ mA}$ $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	175	225	310	$\mu\text{A}$
DYNAMIC PERFORMANCE						
Slew Rate	SR	$R_L = 10 \text{ k}\Omega$ , $A_V = 1$	0.28			$\text{V}/\mu\text{s}$
Gain Bandwidth Product	GBP	$C_L = 35 \text{ pF}$ , $A_V = 1$	580			kHz
Phase Margin	$\Phi_M$	$C_L = 35 \text{ pF}$ , $A_V = 1$	72			Degrees
NOISE PERFORMANCE						
Voltage Noise	$e_n \text{ p-p}$	$f = 0.1 \text{ Hz}$ to $10 \text{ Hz}$	0.2			$\mu\text{V p-p}$
Voltage Noise Density	$e_n$	$f = 1 \text{ kHz}$	12			$\text{nV}/\sqrt{\text{Hz}}$
Uncorrelated Current Noise Density	$i_n$	$f = 1 \text{ kHz}$	0.15			$\text{pA}/\sqrt{\text{Hz}}$
Correlated Current Noise Density	$i_n$	$f = 1 \text{ kHz}$	0.07			$\text{pA}/\sqrt{\text{Hz}}$

## ABSOLUTE MAXIMUM RATINGS

Table 4.

Parameter	Rating
Supply Voltage	$\pm 18\text{ V}$
Input Voltage	$\pm V_{\text{supply}}$
Input Current <sup>1</sup>	$\pm 10\text{ mA}$
Differential Input Voltage <sup>2</sup>	$\pm 10\text{ V}$
Output Short-Circuit Duration to GND	Indefinite
Storage Temperature Range	$-65^{\circ}\text{C}$ to $+150^{\circ}\text{C}$
Operating Temperature Range	$-40^{\circ}\text{C}$ to $+125^{\circ}\text{C}$
Junction Temperature Range	$-65^{\circ}\text{C}$ to $+150^{\circ}\text{C}$
Lead Temperature (Soldering, 60 sec)	300°C

<sup>1</sup>The input pins have clamp diodes to the power supply pins. The input current should be limited to 10 mA or less whenever input signals exceed the power supply rail by 0.5 V.

<sup>2</sup>Differential input voltage is limited to 10 V or the supply voltage, whichever is less.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## THERMAL RESISTANCE

$\theta_{JA}$  is specified for the worst-case conditions, that is, a device soldered in a circuit board for surface-mount packages. This was measured using a standard 4-layer board.

Table 5. Thermal Resistance

Package Type	$\theta_{JA}$	$\theta_{JC}$	Unit
8-Lead SOIC_N (R-8)	158	43	$^{\circ}\text{C/W}$
8-Lead MSOP (RM-8)	185	53	$^{\circ}\text{C/W}$

## ESD CAUTION



### ESD (electrostatic discharge) sensitive device.

Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

## TYPICAL PERFORMANCE CHARACTERISTICS

$T_A = 25^\circ\text{C}$ , unless otherwise noted.

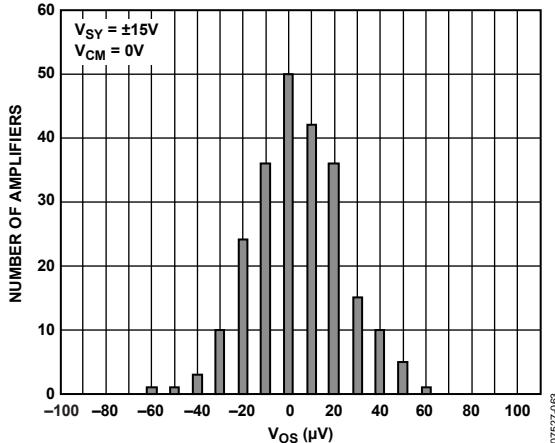


Figure 3. Input Offset Voltage Distribution

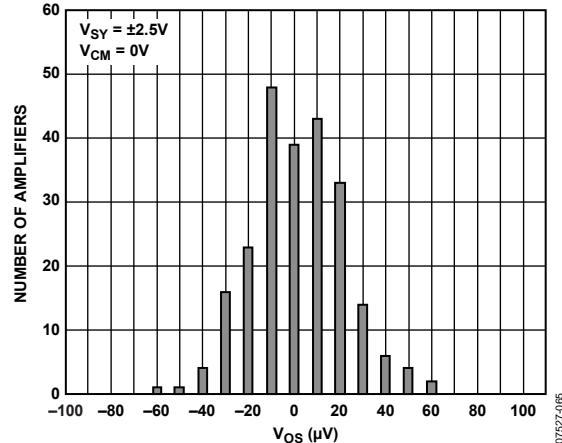


Figure 6. Input Offset Voltage Distribution

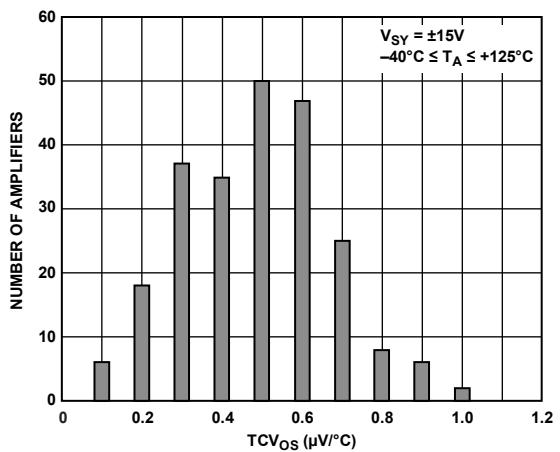


Figure 4. Input Offset Voltage Drift Distribution

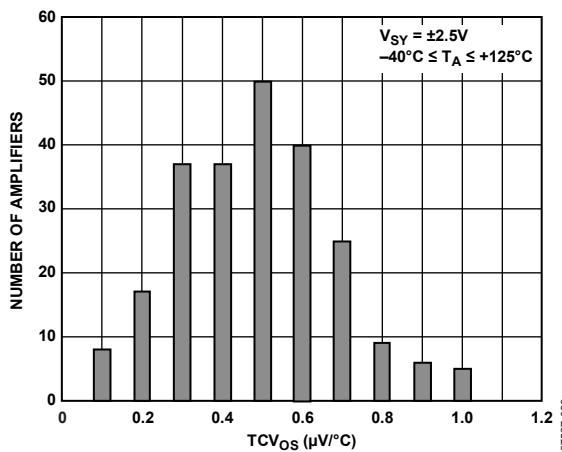


Figure 7. Input Offset Voltage Drift Distribution

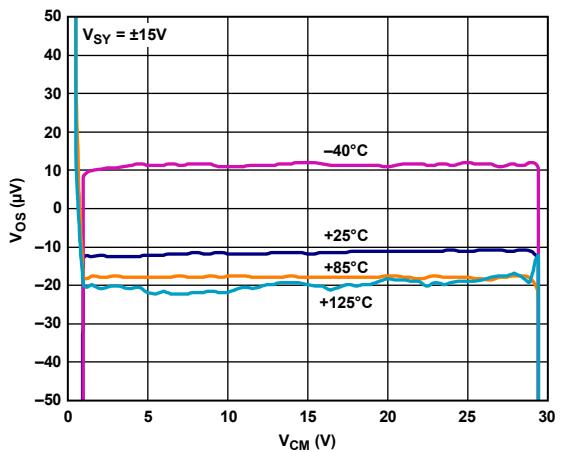


Figure 5. Input Offset Voltage vs. Common-Mode Voltage

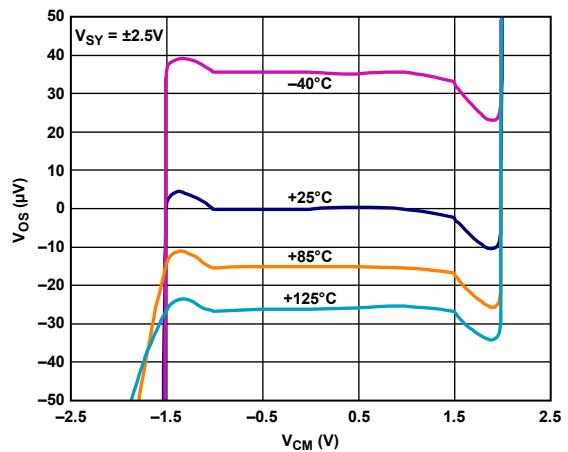


Figure 8. Input Offset Voltage vs. Common-Mode Voltage

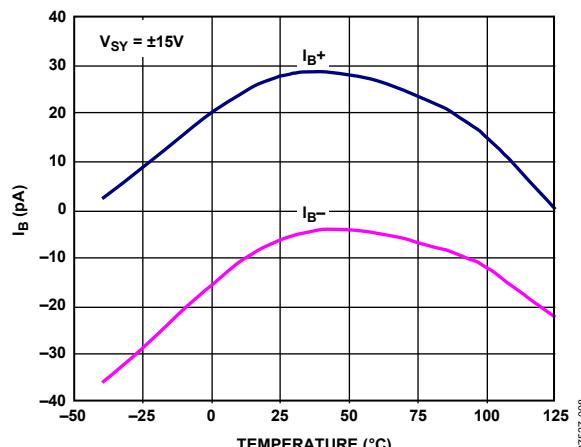


Figure 9. Input Bias Current vs. Temperature

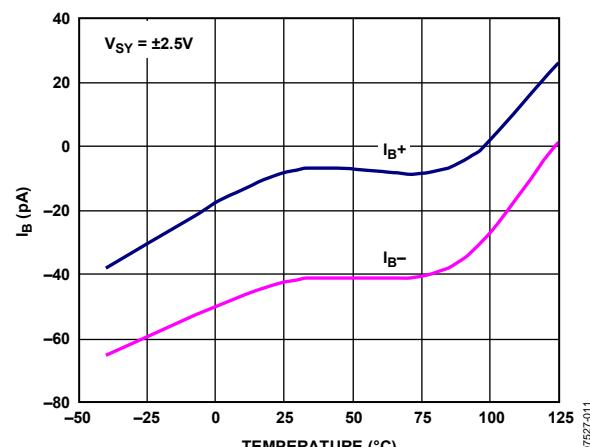


Figure 12. Input Bias Current vs. Temperature

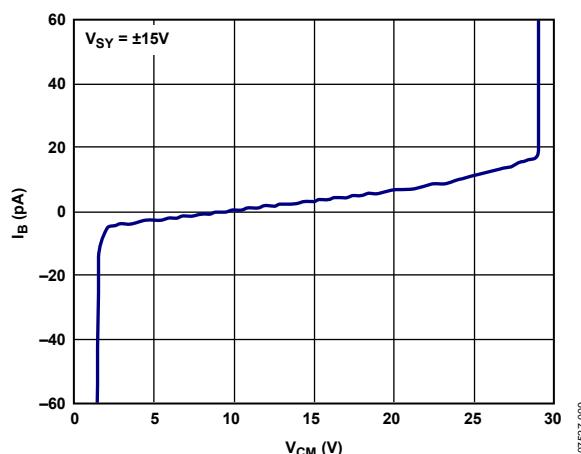


Figure 10. Input Bias Current vs. Common-Mode Voltage

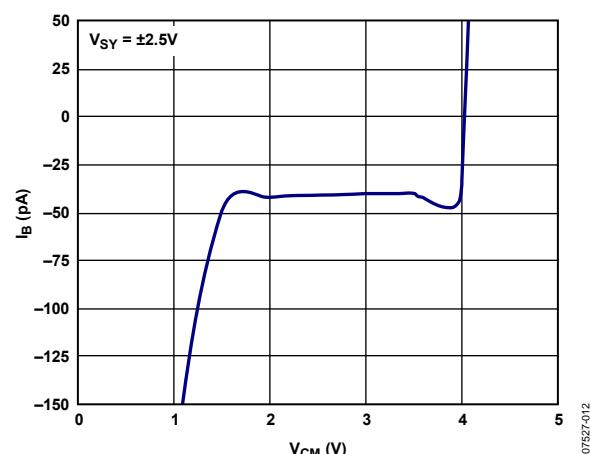


Figure 13. Input Bias Current vs. Common-Mode Voltage

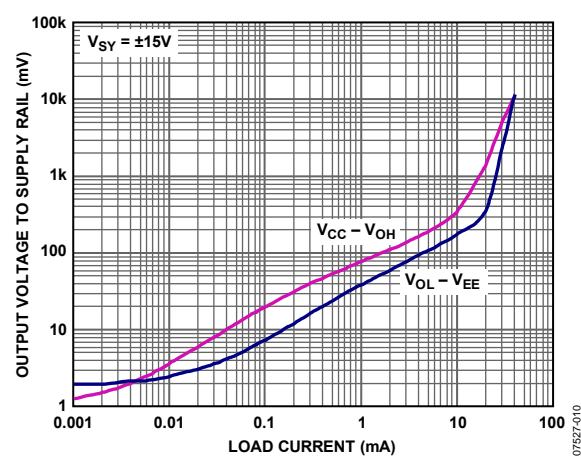


Figure 11. Output Voltage to Supply Rail vs. Load Current

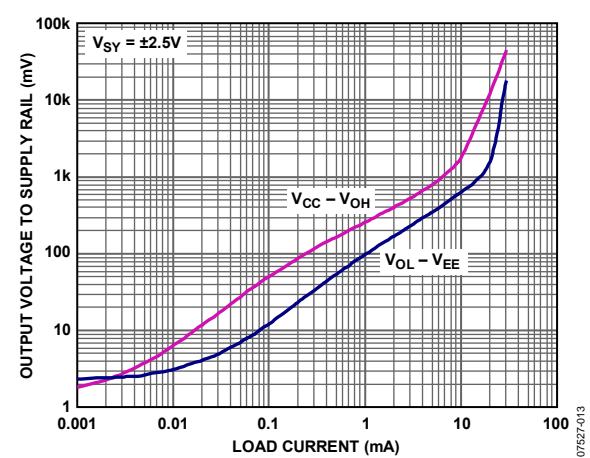


Figure 14. Output Voltage to Supply Rail vs. Load Current

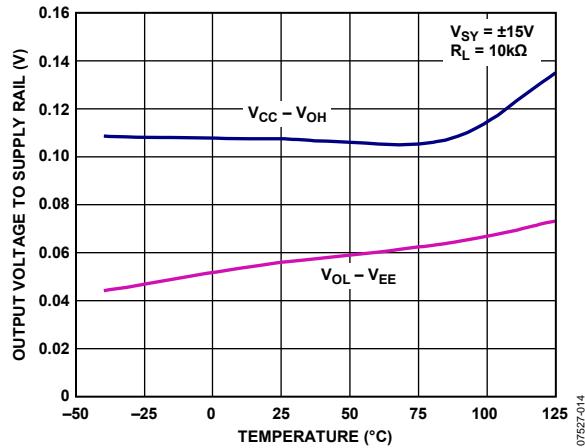


Figure 15. Output Voltage to Supply Rail vs. Temperature

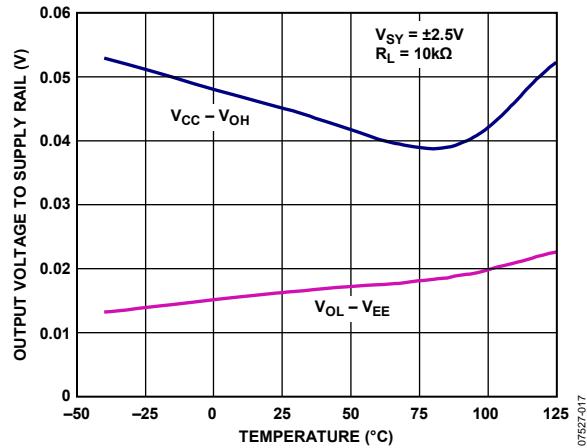


Figure 18. Output Voltage to Supply Rail vs. Temperature

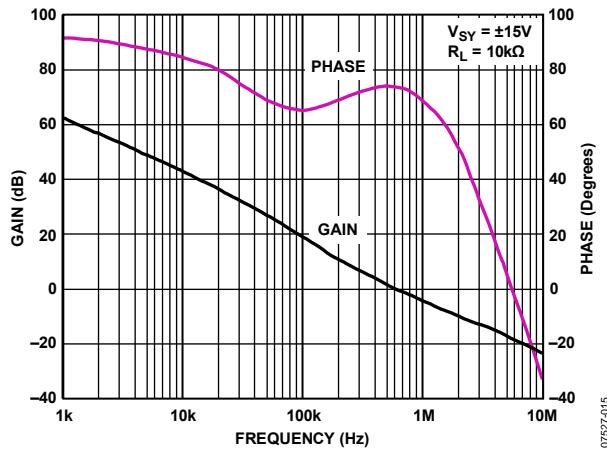


Figure 16. Open-Loop Gain and Phase vs. Frequency

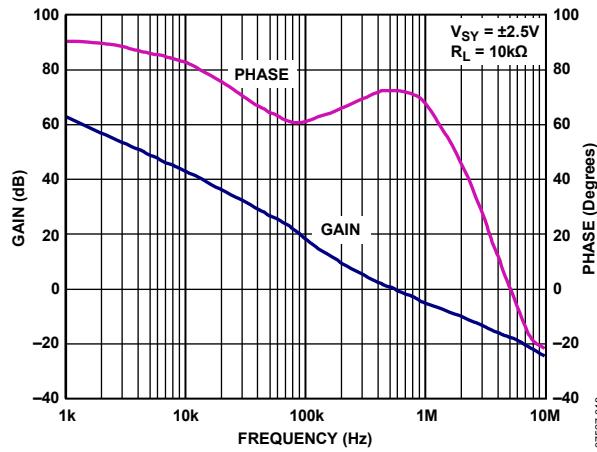


Figure 19. Open-Loop Gain and Phase vs. Frequency

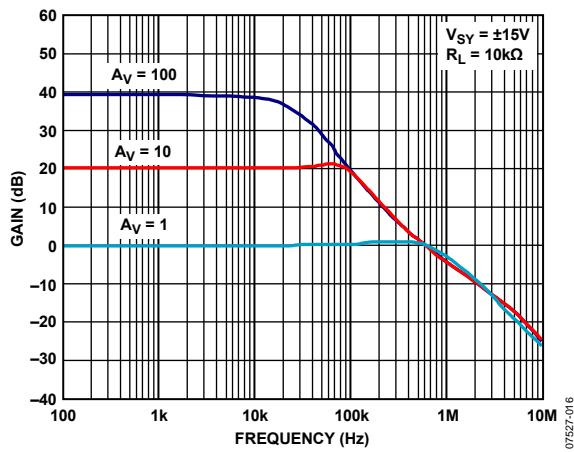


Figure 17. Closed-Loop Gain vs. Frequency

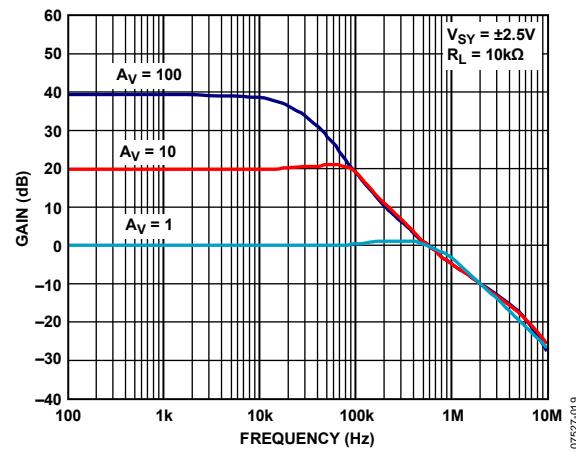
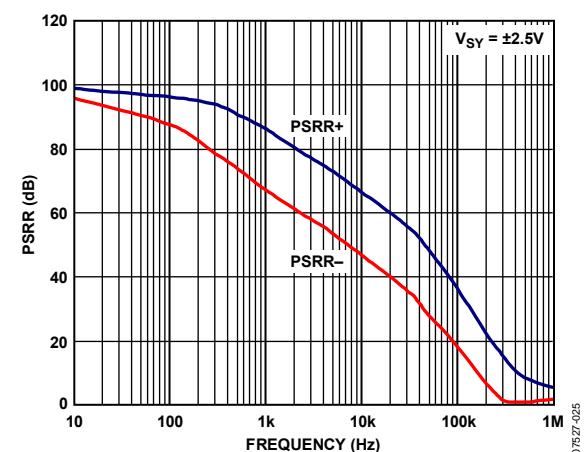
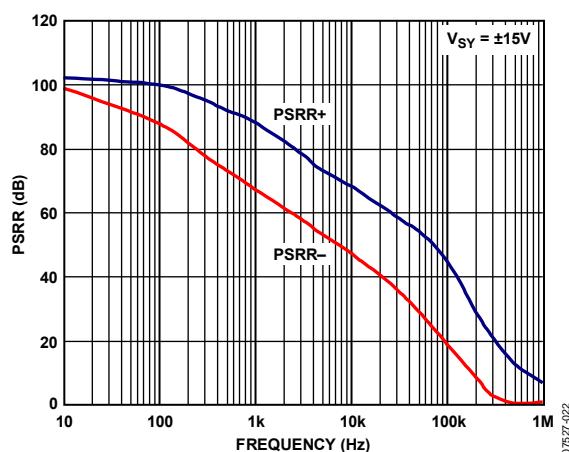
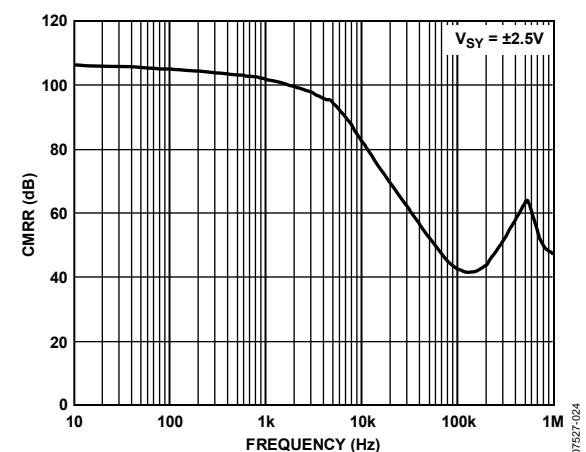
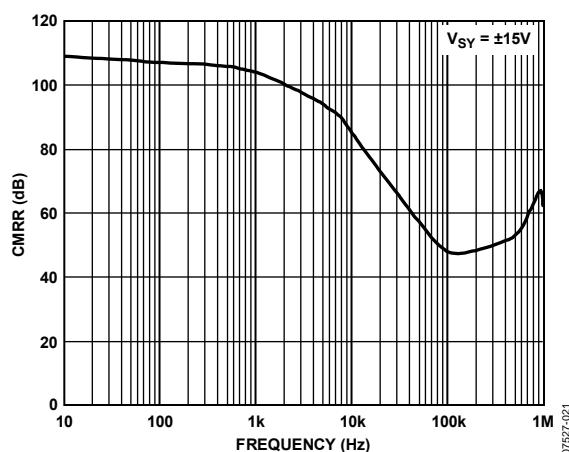
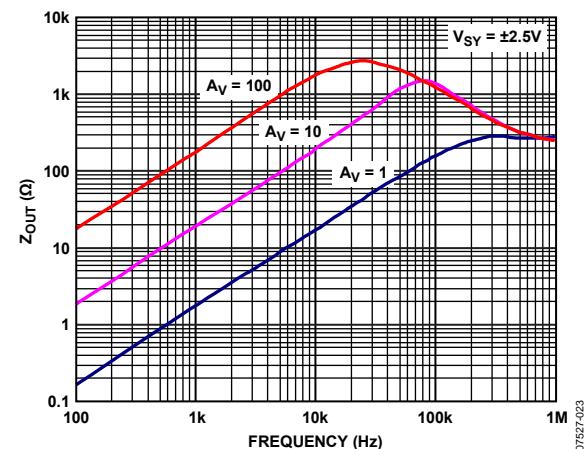
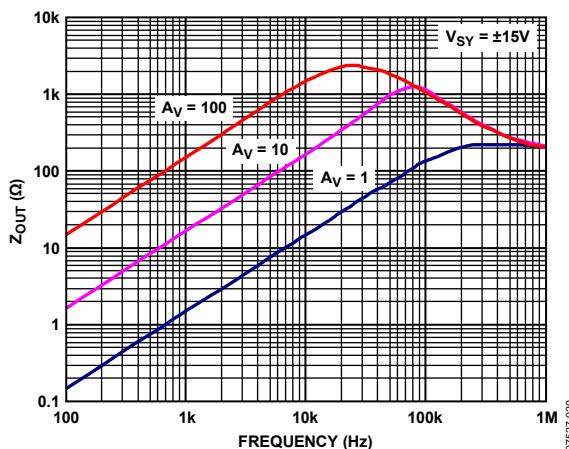


Figure 20. Closed-Loop Gain vs. Frequency



# AD8622

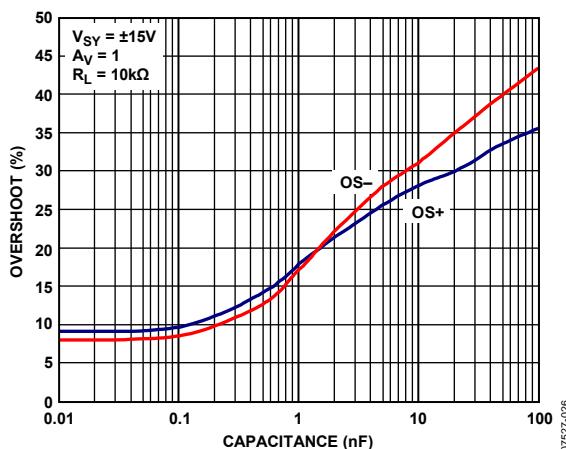


Figure 27. Small-Signal Overshoot vs. Load Capacitance

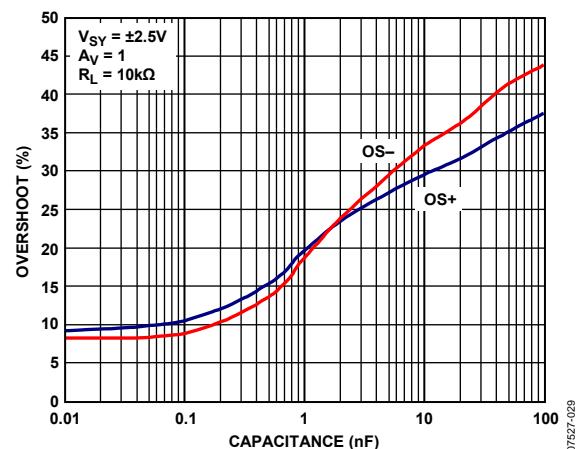


Figure 30. Small-Signal Overshoot vs. Load Capacitance

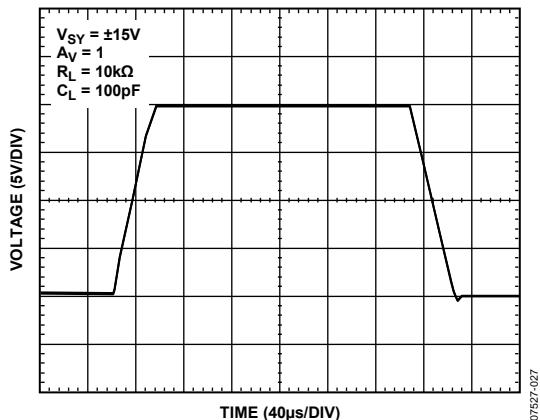


Figure 28. Large-Signal Transient Response

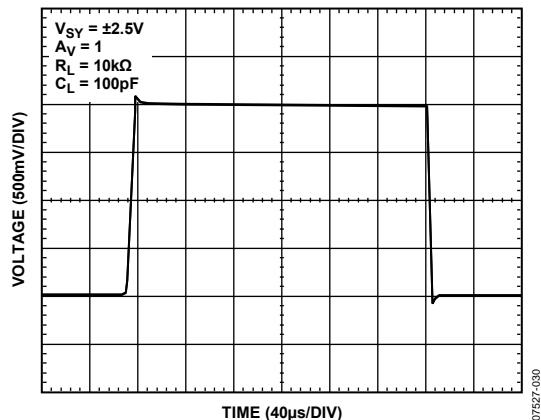


Figure 31. Large-Signal Transient Response

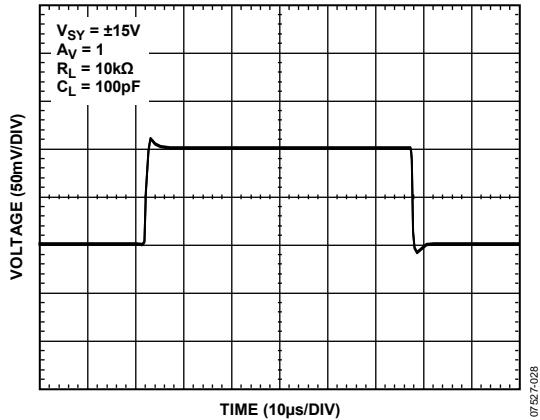


Figure 29. Small-Signal Transient Response

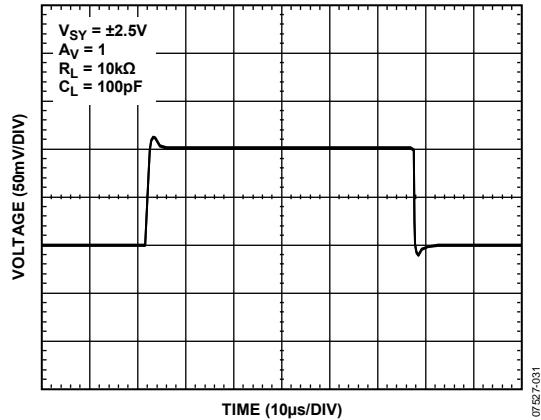


Figure 32. Small-Signal Transient Response

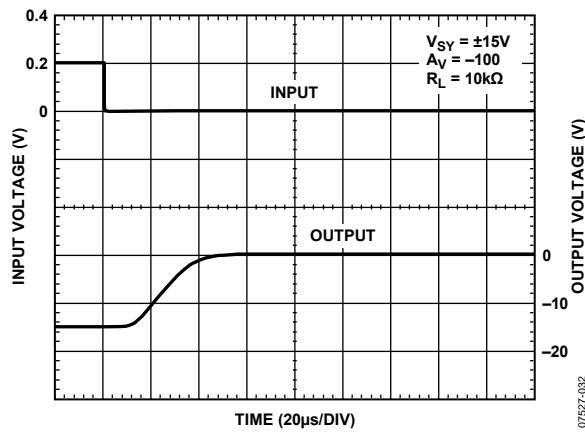


Figure 33. Negative Overload Recovery

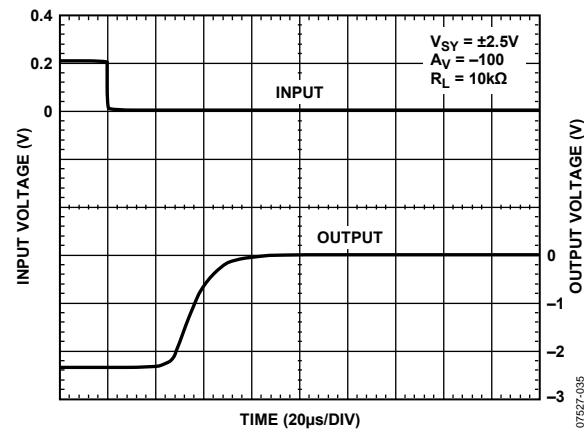


Figure 36. Negative Overload Recovery

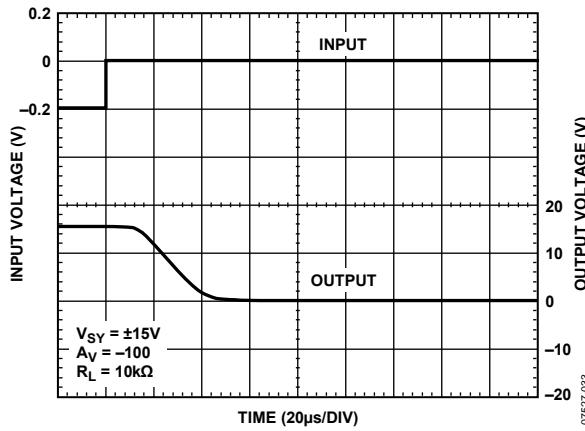


Figure 34. Positive Overload Recovery

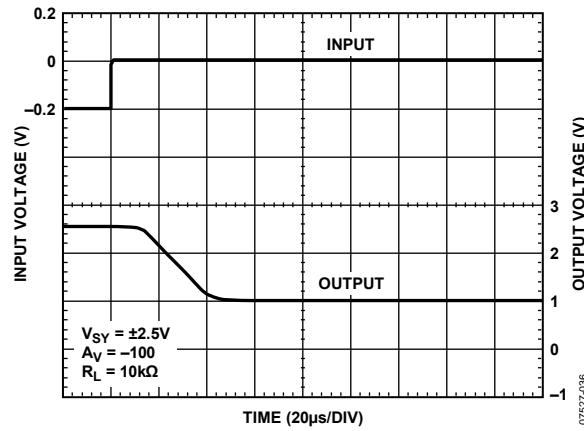


Figure 37. Positive Overload Recovery

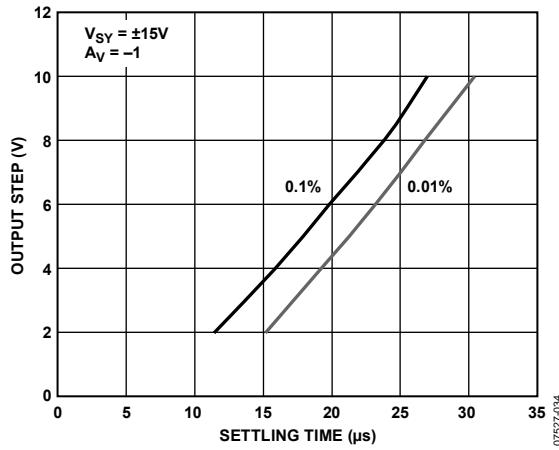


Figure 35. Output Step vs. Settling Time

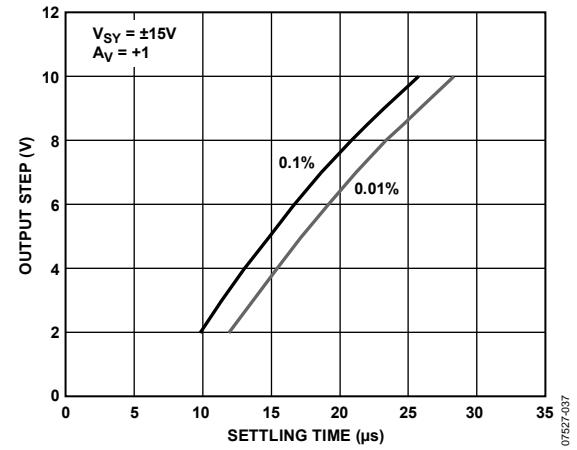


Figure 38. Output Step vs. Settling Time

# AD8622

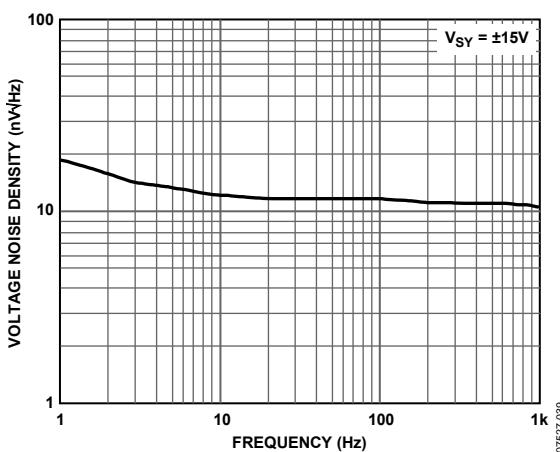


Figure 39. Voltage Noise Density vs. Frequency

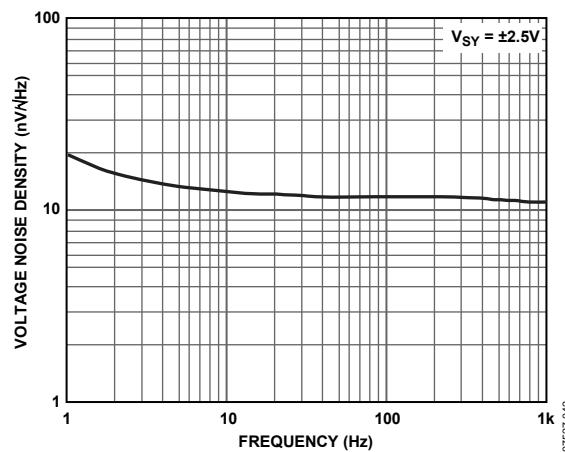


Figure 42. Voltage Noise Density vs. Frequency

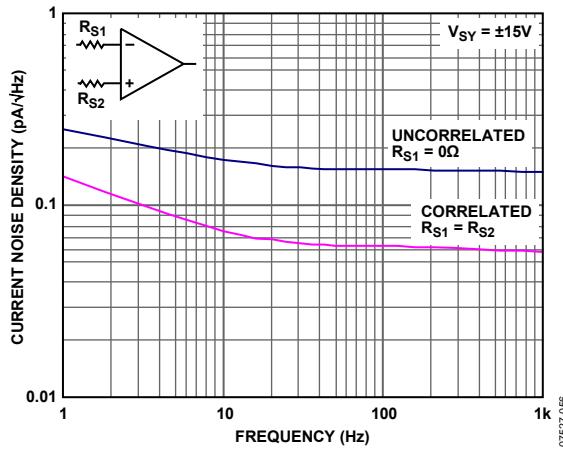


Figure 40. Current Noise Density vs. Frequency

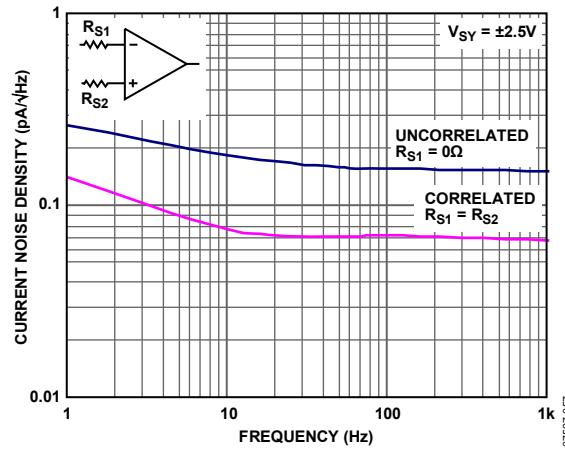


Figure 43. Current Noise Density vs. Frequency

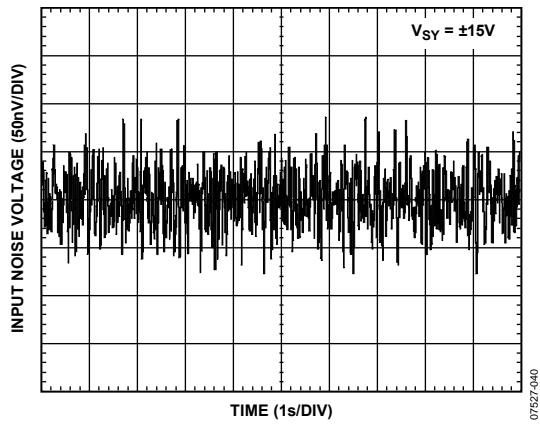


Figure 41. 0.1 Hz to 10 Hz Noise

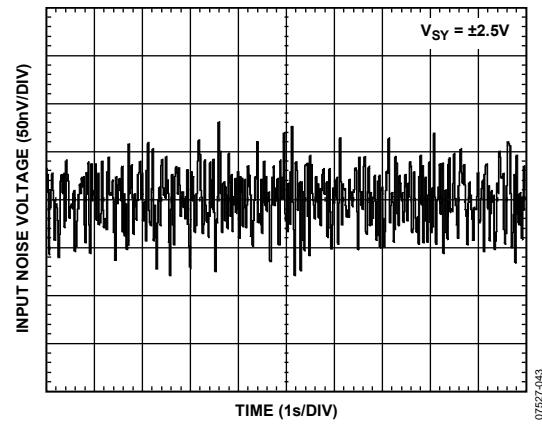
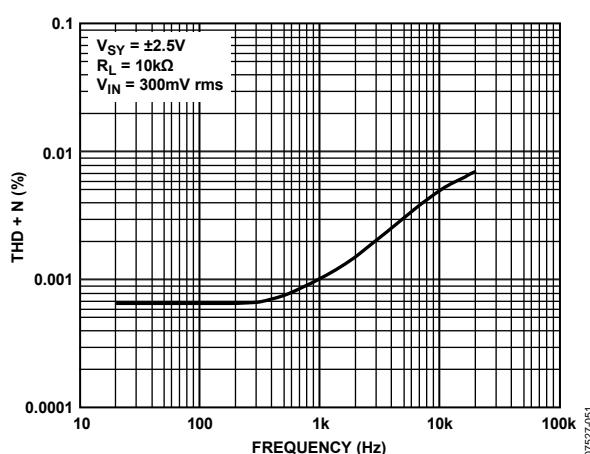
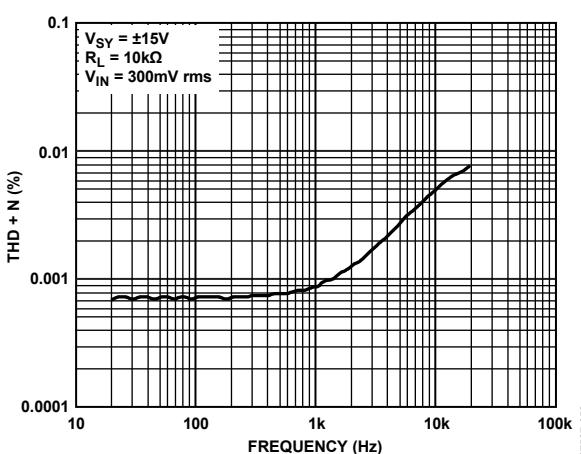
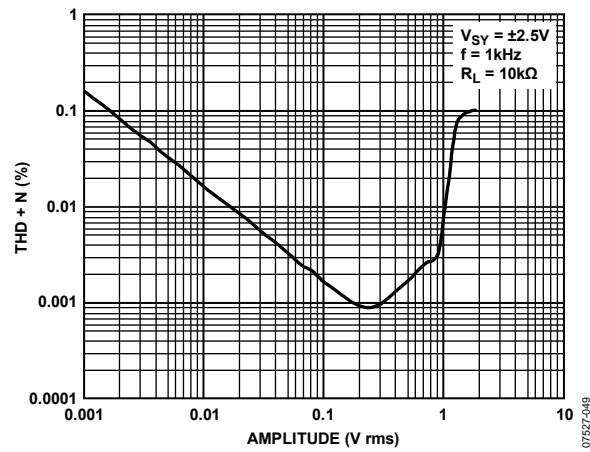
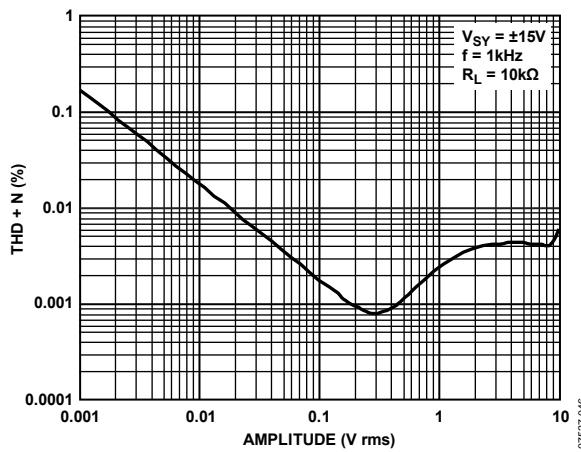
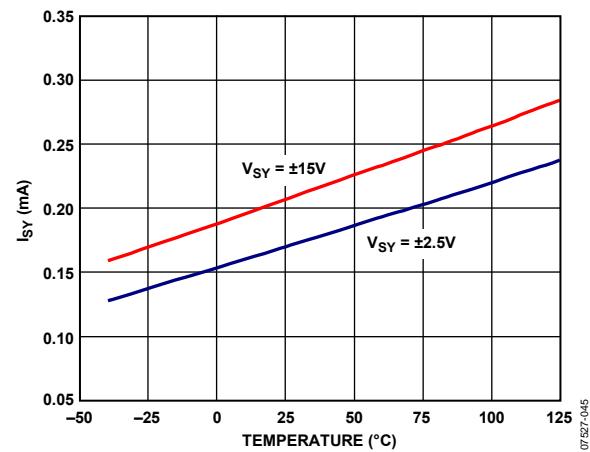
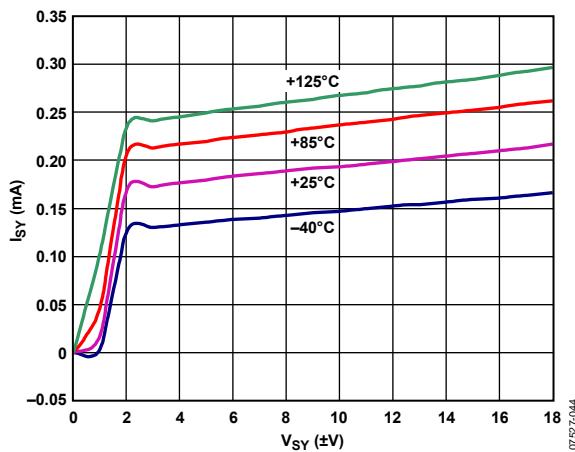


Figure 44. 0.1 Hz to 10 Hz Noise



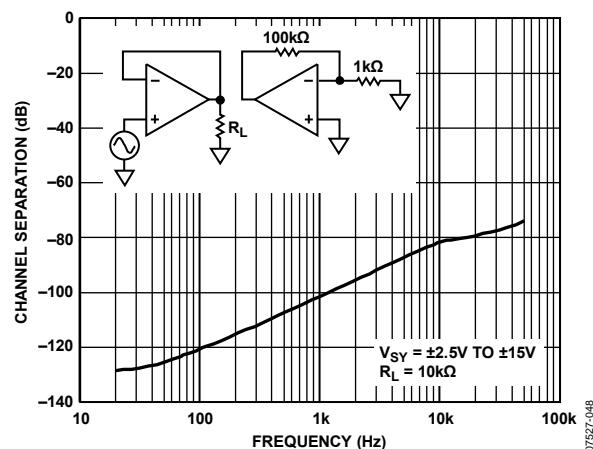


Figure 51. Channel Separation vs. Frequency

## APPLICATIONS INFORMATION

### INPUT PROTECTION

The maximum differential input voltage that can be applied to the AD8622 is determined by the internal diodes connected across its inputs and series resistors at each input. These internal diodes and series resistors limit the maximum differential input voltage to  $\pm 10$  V and are needed to prevent base-emitter junction breakdown from occurring in the input stage of the AD8622 when very large differential voltages are applied. In addition, the internal resistors limit the currents that flow through the diodes. However, in applications where large differential voltages can be inadvertently applied to the device, large currents may still flow through these diodes. In such a case, external resistors must be placed at both inputs of the op amp to limit the input currents to  $\pm 10$  mA (see Figure 52).

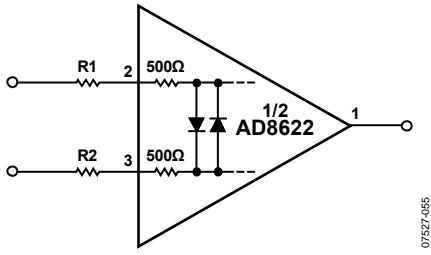


Figure 52. Input Protection

### PHASE REVERSAL

An undesired phenomenon, phase reversal (also known as phase inversion) occurs in many op amps when one or both of the inputs are driven beyond the specified input voltage range (IVR), in effect reversing the polarity of the output. In some cases, phase reversal can induce lockups and even cause equipment damage as well as self destruction.

The AD8622 amplifiers have been carefully designed to prevent output phase reversal when both inputs are maintained within the specified input voltage range. In addition, even if one or both inputs exceed the input voltage range but remain within the supply rails, the output still does not phase reverse. Figure 53 shows the input/output waveforms of the AD8622 configured as a unity-gain buffer with a supply voltage of  $\pm 15$  V.

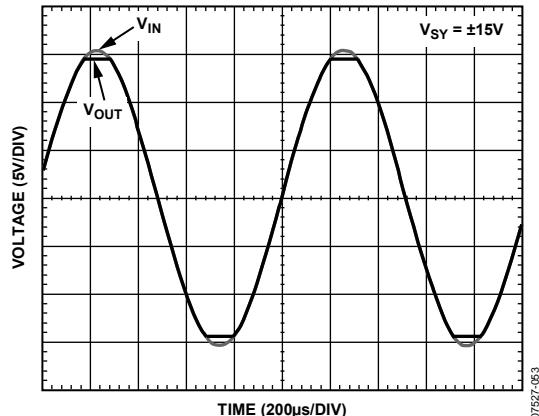
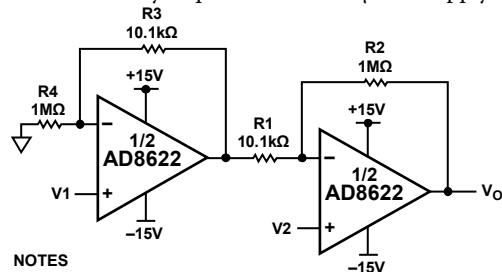


Figure 53. No Phase Reversal

### MICROPOWER INSTRUMENTATION AMPLIFIER

The AD8622 is a dual, high precision, rail-to-rail output op amp operating at just 215  $\mu$ A quiescent current per amplifier. Its ultralow offset, offset drift, and voltage noise, combined with its very low bias current and high common-mode rejection ratio (CMRR), are ideally suited for high accuracy and micropower instrumentation amplifier.

Figure 54 shows the classic 2-op-amp instrumentation amplifier with four resistors using the AD8622. The key to high CMRR for this instrumentation amplifier are resistors that are well matched from both the resistive ratio and the relative drift. For true difference amplification, matching of the resistor ratio is very important, where  $R_3/R_4 = R_1/R_2$ . Assuming perfectly matched resistors, the gain of the circuit is  $1 + R_2/R_1$ , which is approximately 100. Tighter matching of two op amps in one package, like the AD8622, offers a significant boost in performance over the classical 3-op-amp configuration. Overall, the circuit only requires about 430  $\mu$ A of supply current.



#### NOTES

1.  $V_O = 100(V_2 - V_1)$
2. TYPICAL:  $0.01mV < |V_2 - V_1| < 149.7mV$
3. TYPICAL:  $-14.97V < V_O < +14.97V$
4. USE MATCHED RESISTORS.

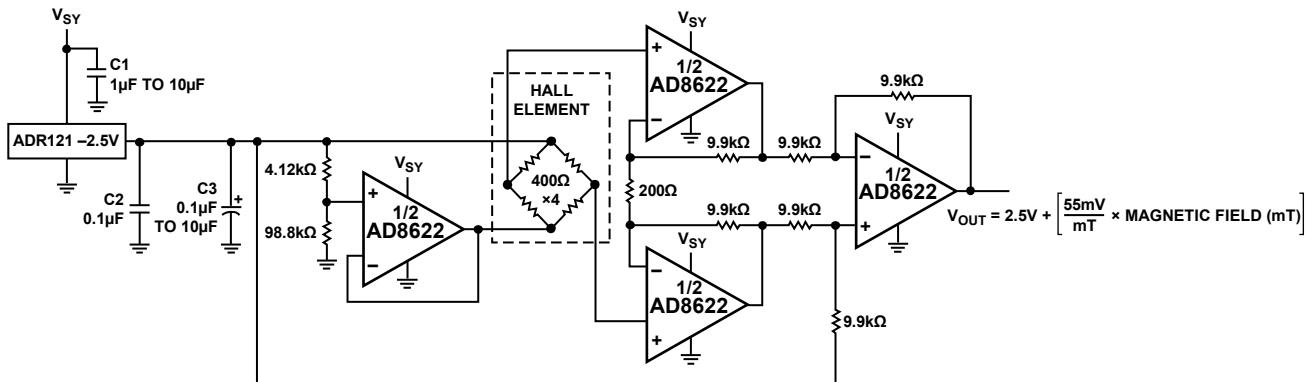
07527-054

Figure 54. Micropower Instrumentation Amplifier

## HALL SENSOR SIGNAL CONDITIONING

The AD8622 is also highly suitable for high accuracy, low power signal conditioning circuits. One such use is in Hall sensor signal conditioning (see Figure 55). The magnetic sensitivity of a Hall element is proportional to the bias voltage applied across it. With 1 V bias voltage, the Hall element consumes about 2.5 mA of supply current and has a sensitivity of 5.5 mV/mT typical. To reduce power consumption, bias voltage must be reduced, but at the risk of lower sensitivity. The only way to achieve higher sensitivity is by introducing a gain using a precision micropower amplifier. The AD8622, with all its features, is well suited to amplify the sensitivity of the Hall element.

The ADR121 is a precision micropower 2.5 V voltage reference. A precision voltage reference is required to hold a constant current so that the Hall voltage only depends on the intensity of the magnetic field. Using the 4.12k:98.8k resistive divider, the bias voltage of the Hall element is reduced to 100 mV, leading to only 250  $\mu$ A of power consumption. The 3-op-amp in-amp configuration of the AD8622 then increases the sensitivity to 55 mV/mT. Using the AD8622 to amplify the sensor signal can reduce power while also achieving higher sensitivity. The total current consumed is just 1.2 mA, resulting in 21 $\times$  improvement in sensitivity/power.



### NOTES

1. USE MATCHED RESISTORS FOR IN-AMP.
2. FOR INFORMATION ON C1, C2, AND C3, REFER TO ADR121 DATA SHEET.

07527452

Figure 55. Hall Sensor Signal Conditioning

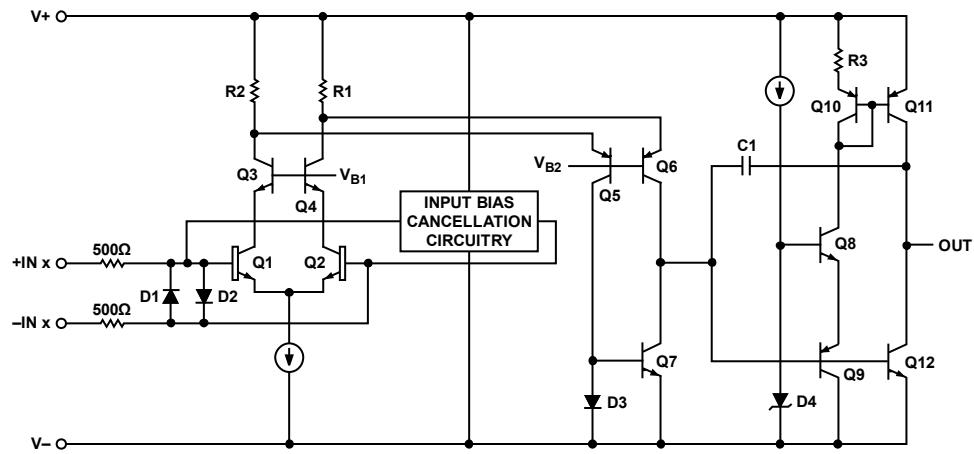
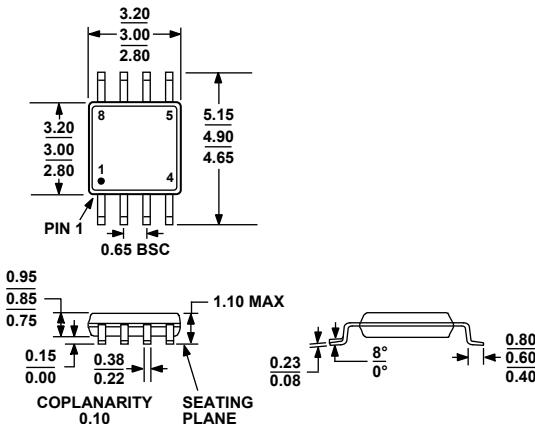
**SIMPLIFIED SCHEMATIC**

Figure 56. Simplified Schematic

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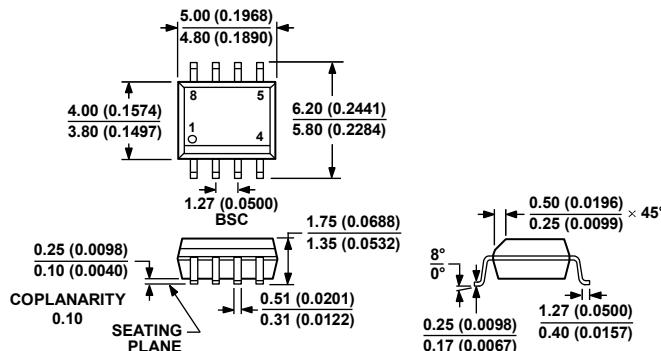
## OUTLINE DIMENSIONS



COMPLIANT TO JEDEC STANDARDS MO-187-AA

Figure 57. 8-Lead Mini Small Outline Package [MSOP]  
(RM-8)

Dimensions shown in millimeters



COMPLIANT TO JEDEC STANDARDS MS-012-AA

CONTROLLING DIMENSIONS ARE IN MILLIMETERS; INCH DIMENSIONS  
(IN PARENTHESES) ARE ROUNDED-OFF MILLIMETER EQUIVALENTS FOR  
REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN.

012407-A

Figure 58. 8-Lead Standard Small Outline Package [SOIC\_N]  
Narrow Body  
(R-8)

Dimensions shown in millimeters and (inches)

## ORDERING GUIDE

Model	Temperature Range	Package Description	Package Option	Branding
AD8622ARMZ <sup>1</sup>	-40°C to +125°C	8-Lead MSOP	RM-8	A1P
AD8622ARMZ-REEL <sup>1</sup>	-40°C to +125°C	8-Lead MSOP	RM-8	A1P
AD8622ARMZ-R7 <sup>1</sup>	-40°C to +125°C	8-Lead MSOP	RM-8	A1P
AD8622ARZ <sup>1</sup>	-40°C to +125°C	8-Lead SOIC_N	R-8	
AD8622ARZ-REEL <sup>1</sup>	-40°C to +125°C	8-Lead SOIC_N	R-8	
AD8622ARZ-REEL7 <sup>1</sup>	-40°C to +125°C	8-Lead SOIC_N	R-8	

<sup>1</sup> Z = RoHS Compliant Part.

**AD8622**

## **NOTES**

**NOTES**